HiPerFET™ Power MOSFETs

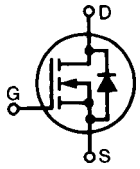
N-Channel Enhancement Mode
High dv/dt, Low t_{rr}, HDMOS™ Family

Obsolete: IXFM35N30

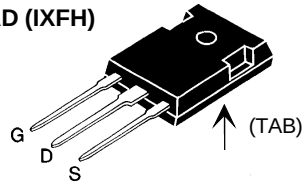
IXFH/~~IXFM~~35N30
IXFH40N30
IXFM40N30

V_{DSS}	I_{D25}	$R_{DS(on)}$
300 V	35 A	100 mΩ
300 V	40 A	85 mΩ
300 V	40 A	88 mΩ

$t_{rr} \leq$ 200 ns

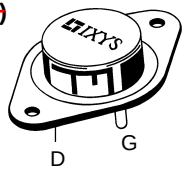


TO-247 AD (IXFH)



~~TO-204 AE (IXFM)~~

Package unavailable



G = Gate, D = Drain,
S = Source, TAB = Drain

Symbol	Test Conditions		Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C		300	V
V_{DGR}	T_J = 25°C to 150°C; R_{GS} = 1 MΩ		300	V
V_{GS}	Continuous		±20	V
V_{GSM}	Transient		±30	V
I_{D25}	T_C = 25°C	35N30 40N30	35 40	A A
I_{DM}	T_C = 25°C, pulse width limited by T_{JM}	35N30 40N30	140 160	A A
I_{AR}	T_C = 25°C	35N30 40N30	35 40	A A
E_{AR}	T_C = 25°C		30	mJ
dv/dt	$I_S \leq I_{DM}$, di/dt ≤ 100 A/µs, $V_{DD} \leq V_{DSS}$, $T_J \leq$ 150°C, R_G = 2 Ω		5	V/ns
P_D	T_C = 25°C		300	W
T_J			-55 ... +150	°C
T_{JM}			150	°C
T_{stg}			-55 ... +150	°C
T_L	1.6 mm (0.062 in.) from case for 10 s		300	°C
M_d	Mounting torque		1.13/10	Nm/lb.in.
Weight			TO-204 = 18 g, TO-247 = 6 g	

Symbol	Test Conditions		Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
V_{DSS}	V_{GS} = 0 V, I_D = 250 µA		300			V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 4 mA		2		4	V
I_{GSS}	V_{GS} = ±20 V_{DC}, V_{DS} = 0				±100	nA
I_{DSS}	V_{DS} = 0.8 • V_{DSS} V_{GS} = 0 V	T_J = 25°C T_J = 125°C			200 1	µA mA
$R_{DS(on)}$	V_{GS} = 10 V, I_D = 0.5 I_{D25} Pulse test, t ≤ 300 µs, duty cycle d ≤ 2 %	35N30 FH40N30 FM40N30			0.100 0.085 0.088	Ω Ω Ω

Features

- International standard packages
- Low $R_{DS\ (on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
  - easy to drive and to protect
- Fast intrinsic Rectifier

Applications

- DC-DC converters
- Synchronous rectification
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor control
- Temperature and lighting controls
- Low voltage relays

Advantages

- Easy to mount with 1 screw (TO-247) (isolated mounting screw hole)
- Space savings
- High power density

IXYS reserves the right to change limits, test conditions, and dimensions.

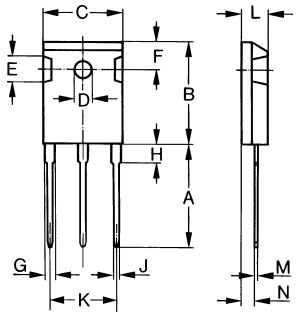
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Symbol	Test Conditions	Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
g_{fs}	V_{DS} = 10 V; I_D = 0.5 I_{D25}, pulse test	22	25		S
C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		4800		pF
C_{oss}			745		pF
C_{rss}			280		pF
$t_{d(on)}$	V_{GS} = 10 V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 I_{D25} R_G = 2 Ω (External)		20	30	ns
t_r			60	90	ns
$t_{d(off)}$			75	100	ns
t_f			45	90	ns
$Q_{g(on)}$	V_{GS} = 10 V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 I_{D25}		177	200	nC
Q_{gs}			28	50	nC
Q_{gd}			78	105	nC
R_{thJC}				0.42	K/W
R_{thCK}			0.25		K/W

Source-Drain Diode

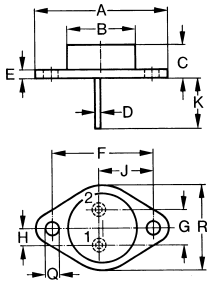
Symbol	Test Conditions		Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
I_S	V_{GS} = 0 V	35N30			35	A
		40N30			40	A
I_{SM}	Repetitive; pulse width limited by T_{JM}	35N30			140	A
		40N30			160	A
V_{SD}	I_F = I_S, V_{GS} = 0 V, Pulse test, t ≤ 300 µs, duty cycle d ≤ 2 %				1.5	V
t_{rr}	I_F = I_S, -di/dt = 100 A/µs, V_R = 100 V	T_J = 25°C			200	ns
		T_J = 125°C			350	ns

TO-247 AD (IXFH) Outline



Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.610	0.640
D	3.55	3.65	0.140	0.144
E	4.32	5.49	0.170	0.216
F	5.4	6.2	0.212	0.244
G	1.65	2.13	0.065	0.084
H	-	4.5	-	0.177
J	1.0	1.4	0.040	0.055
K	10.8	11.0	0.426	0.433
L	4.7	5.3	0.185	0.209
M	0.4	0.8	0.016	0.031
N	1.5	2.49	0.087	0.102

TO-204 AE (IXFM) Outline



Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	38.61	39.12	1.520	1.540
B	-	22.22	-	0.875
C	6.40	11.40	0.252	0.449
D	1.45	1.60	0.057	0.063
E	1.52	3.43	0.060	0.135
F	30.15	BSC	1.187	BSC
G	10.67	11.17	0.420	0.440
H	5.21	5.71	0.205	0.225
J	16.64	17.14	0.655	0.675
K	11.18	12.19	0.440	0.480
Q	3.84	4.19	0.151	0.165
R	25.16	26.66	0.991	1.050

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IXYS MOSFETS and IGBTs are covered by one or more of the following U.S. patents:
4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025

Fig.1. Output Characteristics

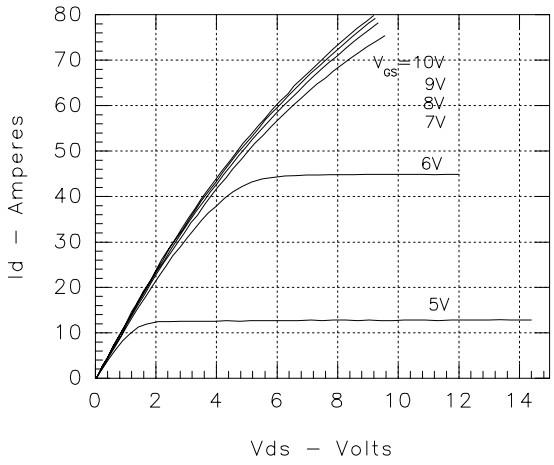


Fig. 2. Input Admittance

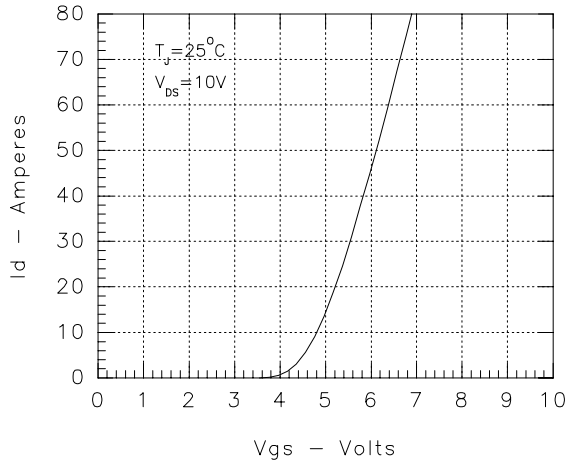


Fig. 3. Rds(on) vs. Drain Current

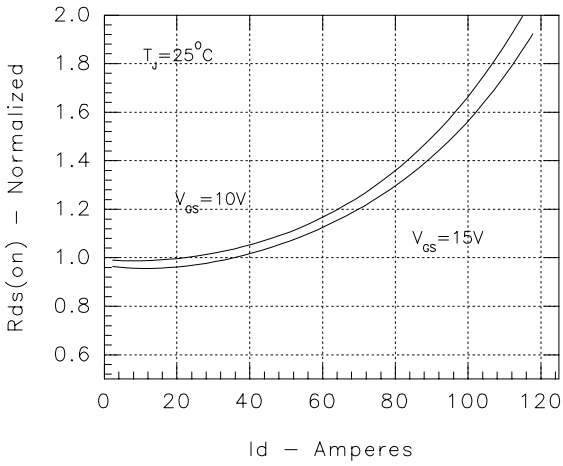


Fig. 4. Temperature Dependence of Drain to Source Resistance

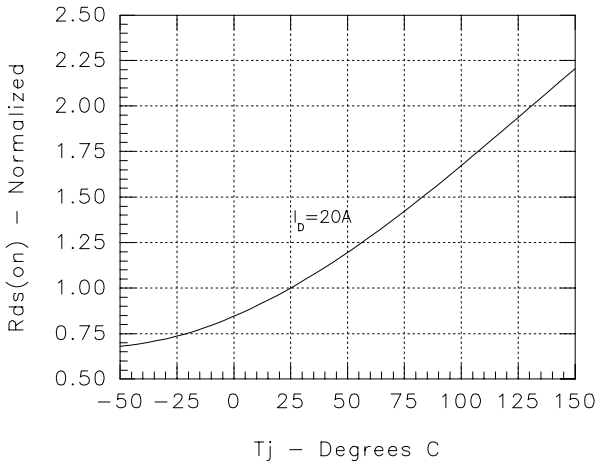


Fig. 5. Drain Current vs. Case Temperature

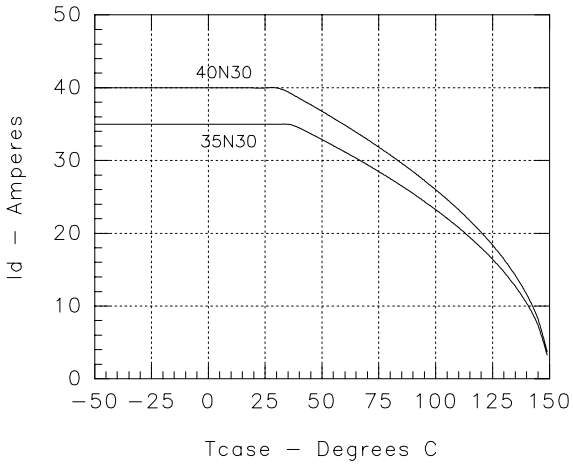
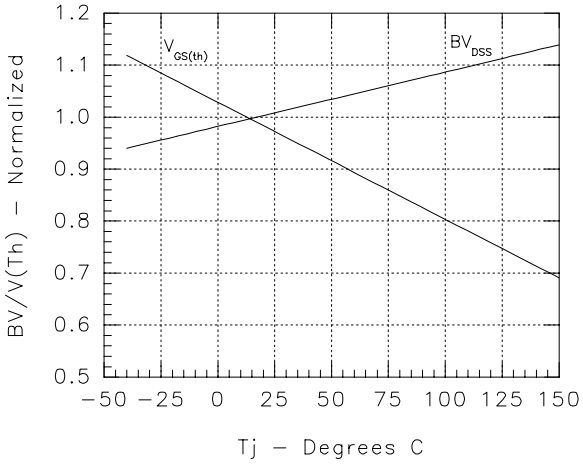


Fig. 6. Temperature Dependence of Breakdown Voltage and Threshold Voltage



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Fig.7 Gate Charge Characteristic Curve

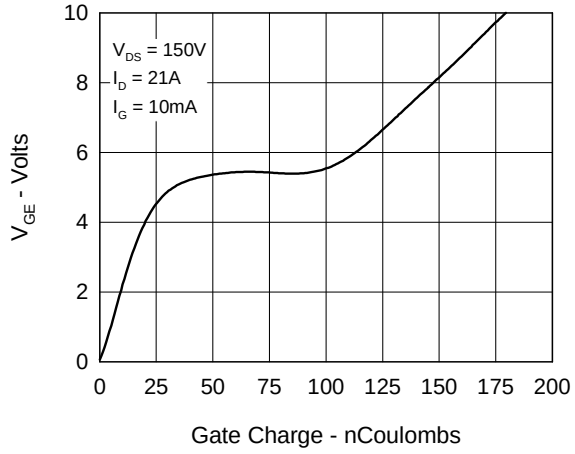


Fig.8 Forward Bias Safe Operating Area

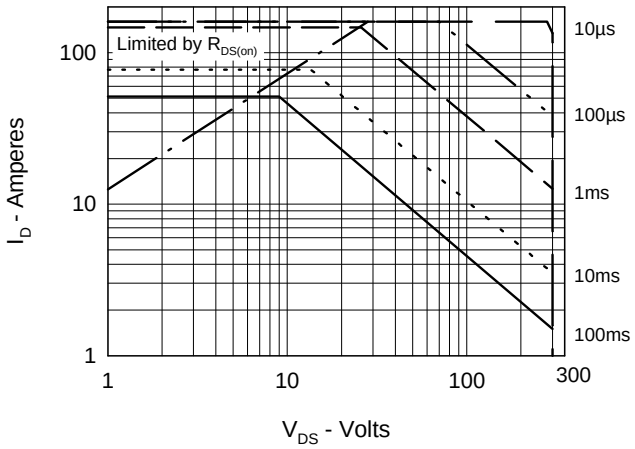


Fig.9 Capacitance Curves

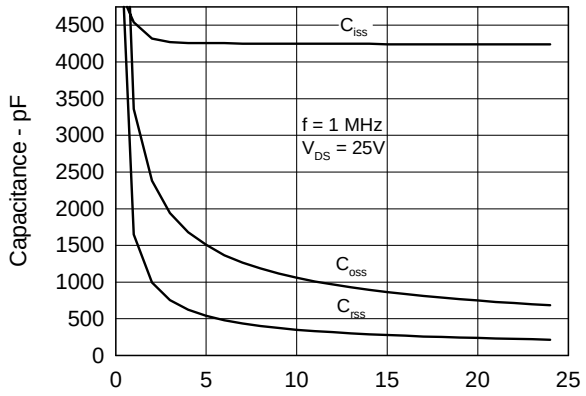


Fig.10 Source Current vs. Source

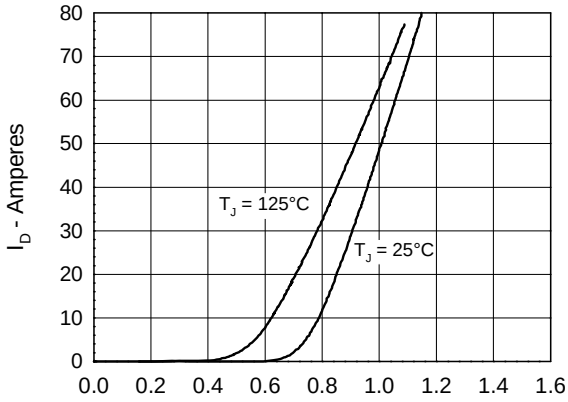
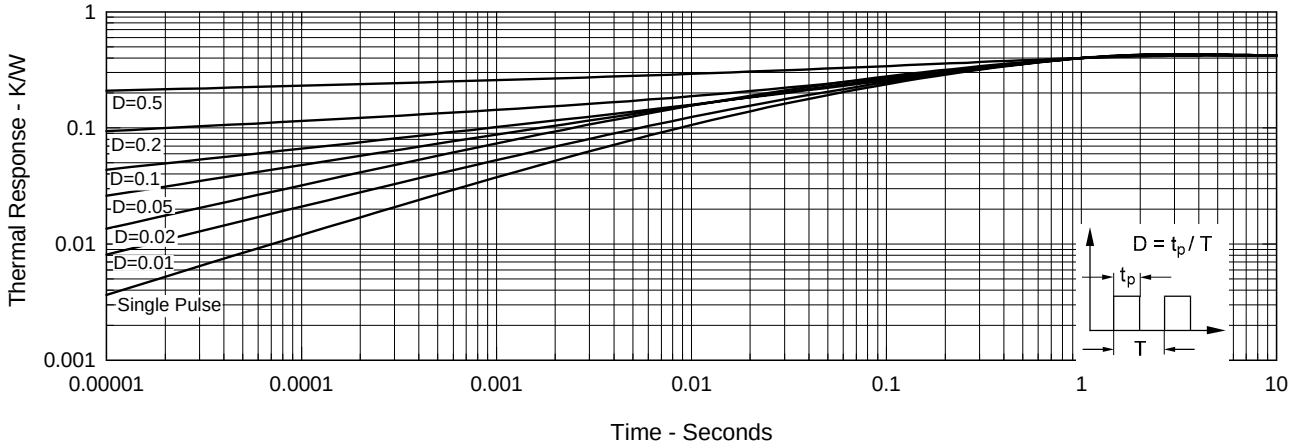


Fig.11 Transient Thermal Impedance



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